## -5 V Differential ECL to TTL Translator

## MC10ELT25, MC100ELT25

## Description

The MC10ELT/100ELT25 is a differential ECL to TTL translator. Because ECL levels are used, a $+5 \mathrm{~V},-5.2 \mathrm{~V}$ (or -4.5 V ) and ground are required. The small outline 8 -lead package and the single gate of the ELT25 makes it ideal for those applications where space, performance and low power are at a premium.

The $\mathrm{V}_{\mathrm{BB}}$ pin, an internally generated voltage supply, is available to this device only. For single-ended input conditions, the unused differential input is connected to $\mathrm{V}_{\mathrm{BB}}$ as a switching reference voltage. $\mathrm{V}_{\mathrm{BB}}$ may also rebias AC coupled inputs. When used, decouple $\mathrm{V}_{\mathrm{BB}}$ and $\mathrm{V}_{\mathrm{CC}}$ via a $0.01 \mu \mathrm{~F}$ capacitor and limit current sourcing or sinking to 0.5 mA . When not used, $\mathrm{V}_{\mathrm{BB}}$ should be left open.

The 100 Series contains temperature compensation.

## Features

- 2.6 ns Typical Propagation Delay
- $100 \mathrm{MHz} \mathrm{F}_{\text {MAX }}$ CLK
- 24 mA TTL Outputs
- Flow Through Pinouts
- Operating Range: $\mathrm{V}_{\mathrm{CC}}=4.5 \mathrm{~V}$ to 5.5 V with $\mathrm{GND}=0 \mathrm{~V}$;
$\mathrm{V}_{\mathrm{EE}}=-4.2 \mathrm{~V}$ to -5.7 V with $\mathrm{GND}=0 \mathrm{~V}$
- Internal Input $50 \mathrm{k} \Omega$ Pulldown Resistors
- Q Output will default HIGH with inputs open or $<1.3 \mathrm{~V}$
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant

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MARKING DIAGRAMS*


SOIC-8 D SUFFIX
CASE 751


TSSOP-8 DT SUFFIX CASE 948R


$$
\begin{array}{ll}
\mathrm{H} & =\text { MC10 } \\
\mathrm{K} & =\text { MC100 } \\
\text { A } & =\text { Assembly Location } \\
\mathrm{L} & =\text { Wafer Lot } \\
\text { Y } & =\text { Year } \\
\mathrm{W} & =\text { Work Week } \\
\text { - } & =\text { Pb-Free Package }
\end{array}
$$

(Note: Microdot may be in either location)
*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| MC10ELT25DG | SOIC-8 <br> $($ Pb-Free $)$ | 98 Units / Tube |
| MC10ELT25DR2G | SOIC-8 <br> $($ Pb-Free $)$ | $2500 /$ <br> Tape \& Reel |
| MC100ELT25DG | SOIC-8 <br> (Pb-Free) | 98 Units / Tube |
| MC100ELT25DR2G | SOIC-8 <br> (Pb-Free) | $2500 /$ <br> Tape \& Reel |
| MC100ELT25DTG | TSSOP-8 <br> (Pb-Free) | 100 Units / Tube |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MC10ELT25, MC100ELT25



Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

| Pin | Function |
| :--- | :--- |
| $D, \bar{D}$ | ECL Differential Inputs |
| Q | TTL Output |
| $V_{B B}$ | Reference Voltage Output |
| $V_{C C}$ | Positive Supply |
| $V_{\text {EE }}$ | Negative Supply |
| GND | Ground |
| NC | No Connect |

Table 2. ATTRIBUTES

| Characteristics | Value |
| :--- | :---: |
| Internal Input Pulldown Resistor | $75 \mathrm{k} \Omega$ |
| Internal Input Pullup Resistor | $\mathrm{N} / \mathrm{A}$ |
| ESD Protection <br> Human Body Model <br> Machine Model |  |
| Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1) | $>1 \mathrm{kV}$ |
| SOIC-8 <br> TSSOP-8 | Pb-Free Pkg |
| Flammability Rating <br> Oxygen Index: 28 to 34 | Level 1 <br> Level 3 |
| Transistor Count | UL 94 V-0 @ 0.125 in |
| Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test | 38 Devices |

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

| Symbol | Parameter | Condition 1 | Condition 2 | Rating | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive Power Supply | GND $=0 \mathrm{~V}$ | $\mathrm{V}_{\mathrm{EE}}=-5.0 \mathrm{~V}$ | 7 | V |
| $\mathrm{V}_{\mathrm{EE}}$ | Negative Power Supply | GND $=0 \mathrm{~V}$ | $\mathrm{V}_{\mathrm{CC}}=+5.0 \mathrm{~V}$ | -8 | V |
| $\mathrm{V}_{\text {IN }}$ | Input Voltage | GND $=0 \mathrm{~V}$ |  | 0 to $\mathrm{V}_{\mathrm{EE}}$ | V |
| $\mathrm{I}_{\text {BB }}$ | $\mathrm{V}_{\text {BB }}$ Sink/Source |  |  | $\pm 0.5$ | mA |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range |  |  | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage Temperature Range |  |  | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | $\begin{aligned} & 0 \text { Ifpm } \\ & 500 \text { lfpm } \end{aligned}$ | $\begin{aligned} & \text { SOIC-8 } \\ & \text { SOIC-8 } \end{aligned}$ | $\begin{aligned} & \hline 190 \\ & 130 \end{aligned}$ | $\begin{aligned} & \hline{ }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{W} \end{aligned}$ |
| $\theta_{\mathrm{Jc}}$ | Thermal Resistance (Junction-to-Case) | Standard Board | SOIC-8 | 41 to 44 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | $\begin{aligned} & \hline 0 \text { lfpm } \\ & 500 \text { lfpm } \end{aligned}$ | $\begin{aligned} & \hline \text { TSSOP-8 } \\ & \text { TSSOP-8 } \end{aligned}$ | $\begin{aligned} & 185 \\ & 140 \end{aligned}$ | $\begin{aligned} & { }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{W} \end{aligned}$ |
| $\theta_{\mathrm{Jc}}$ | Thermal Resistance (Junction-to-Case) | Standard Board | TSSOP-8 | 41 to $44 \pm 5 \%$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{T}_{\text {sol }}$ | Wave Solder Pb-Free | <2 to 3 sec @ 260 ${ }^{\circ} \mathrm{C}$ |  | 265 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
2. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

Table 4. 10ELT SERIES NECL INPUT DC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V} ; \mathrm{V}_{\mathrm{EE}}=-5.0 \mathrm{~V}$; GND $=0 \mathrm{~V}$ (Note 3)

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage (Single-Ended) (Note 4) | -1230 |  | -890 | -1130 |  | -810 | -1060 |  | -720 | mV |
| $\mathrm{V}_{\text {IL }}$ | Input LOW Voltage (Single-Ended) (Note 4) | -1950 |  | -1500 | -1950 |  | -1480 | -1950 |  | -1445 | mV |
| $\mathrm{V}_{\mathrm{BB}}$ | Output Voltage Reference | -1.43 |  | -1.30 | -1.35 |  | -1.25 | -1.31 |  | -1.19 | V |
| $\mathrm{V}_{\text {IHCMR }}$ | Input HIGH Voltage Common Mode Range (Differential) (Notes 4 and 5) | -2.8 |  | 0.0 | -2.8 |  | 0.0 | -2.8 |  | 0.0 | V |
| IIH | Input HIGH Current |  |  | 255 |  |  | 175 |  |  | 175 | $\mu \mathrm{A}$ |
| ILL | Input LOW Current | 0.5 |  |  | 0.5 |  |  | 0.3 |  |  | $\mu \mathrm{A}$ |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
3. Input parameters vary $1: 1$ with $G N D . V_{E E}$ can vary +0.06 V to -0.5 V .
4. TTL output $R_{L}=500 \Omega$ to GND
5. $\mathrm{V}_{\mathrm{IHCMR}}$ min varies $1: 1$ with $\mathrm{V}_{\mathrm{EE}}, \mathrm{V}_{\mathrm{IHCMR}}$ max varies $1: 1$ with $G N D$.

Table 5. 100ELT SERIES NECL INPUT DC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}$; $\mathrm{V}_{\mathrm{EE}}=-5.0 \mathrm{~V}$; GND $=0 \mathrm{~V}$ (Note 6)

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage (Single-Ended) (Note 7) | -1165 |  | -880 | -1165 |  | -880 | -1165 |  | -880 | mV |
| $\mathrm{V}_{\mathrm{IL}}$ | Input LOW Voltage (Single-Ended) (Note 7) | -1810 |  | -1475 | -1810 |  | -1475 | -1810 |  | -1475 | mV |
| $\mathrm{V}_{\mathrm{BB}}$ | Output Voltage Reference | -1.38 |  | -1.26 | -1.38 |  | -1.26 | -1.38 |  | -1.26 | V |
| $\mathrm{V}_{\text {IHCMR }}$ | Input HIGH Voltage Common Mode Range (Differential) (Notes 7 and 8) | -2.8 |  | 0.0 | -2.8 |  | 0.0 | -2.8 |  | 0.0 | V |
| IIH | Input HIGH Current |  |  | 255 |  |  | 175 |  |  | 175 | $\mu \mathrm{A}$ |
| IIL | Input LOW Current | 0.5 |  |  | 0.5 |  |  | 0.5 |  |  | $\mu \mathrm{A}$ |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
6. Input parameters vary $1: 1$ with GND. $\mathrm{V}_{\mathrm{EE}}$ can vary +0.8 V to -0.5 V .
7. TTL output $R_{L}=500 \Omega$ to GND
8. $\mathrm{V}_{\mathrm{IHCMR}}$ min varies $1: 1$ with $\mathrm{V}_{\mathrm{EE}}, \mathrm{V}_{\mathrm{IHCMR}}$ max varies $1: 1$ with $G N D$.

Table 6. TTL OUTPUT DC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=4.5 \mathrm{~V}$ to $5.5 \mathrm{~V} ; \mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$

| Symbol | Characteristic | Condition | Min | Typ | Max | Unit |
| :---: | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage | $\mathrm{I}_{\mathrm{OH}}=-3.0 \mathrm{~mA}$ | 2.4 |  |  | V |
| $\mathrm{~V}_{\mathrm{OL}}$ | Output LOW Voltage | $\mathrm{I}_{\mathrm{OL}}=24 \mathrm{~mA}$ |  |  | 0.5 | V |
| $\mathrm{I}_{\mathrm{CCH}}$ | Power Supply Current |  |  | 11 | 16 | mA |
| $\mathrm{I}_{\mathrm{CCL}}$ | Power Supply Current |  |  | 13 | 18 | mA |
| $\mathrm{I}_{\mathrm{EE}}$ | Negative Power Supply Current |  |  | 15 | 21 | mA |
| $\mathrm{I}_{\mathrm{OS}}$ | Output Short Circuit Current |  | -150 |  | -60 | mA |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 Ifpm.

Table 7. AC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V} ; \mathrm{V}_{\mathrm{EE}}=-5.0 \mathrm{~V} ; \mathrm{GND}=0 \mathrm{~V}$ (Note 9 and Note 10)

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $f_{\text {max }}$ | Maximum Toggle Frequency |  |  |  |  | 100 |  |  |  |  | MHz |
| $\mathrm{t}_{\text {PLH }}$ | Propagation Delay @ 1.5 V | 1.7 |  | 3.6 | 1.7 |  | 3.6 | 1.7 |  | 3.6 | ns |
| $\mathrm{t}_{\text {PHL }}$ | Propagation Delay @ 1.5 V | 2.6 |  | 4.1 | 2.6 |  | 4.1 | 2.6 |  | 4.1 | ns |
| $\mathrm{t}_{\text {IITTER }}$ | Random Clock Jitter (RMS) |  |  |  |  | 35 |  |  |  |  | ps |
| $\mathrm{t}_{\mathrm{r}}$ $\mathrm{t}_{\mathrm{f}}$ | Output Rise/Fall Times QTTL 10\%-90\% |  |  |  |  | $\begin{aligned} & \hline 1.9 \\ & 2.3 \end{aligned}$ |  |  |  |  | ns |
| $\mathrm{V}_{\mathrm{PP}}$ | Input Swing (Note 11) | 200 |  | 1000 | 200 |  | 1000 | 200 |  | 1000 | mV |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 Ifpm.
9. $\mathrm{V}_{\mathrm{CC}}$ can vary $\pm 0.25 \mathrm{~V}$.
$\mathrm{V}_{\text {EE }}$ can vary +0.06 V to -0.5 V for 10ELT; $\mathrm{V}_{\text {EE }}$ can vary +0.8 V to -0.5 V for 100ELT.
10. $\mathrm{R}_{\mathrm{L}}=500 \Omega$ to GND and $\mathrm{C}_{\mathrm{L}}=20 \mathrm{pF}$ to GND. Refer to Figure 2.
11. $\mathrm{V}_{\mathrm{PP}}(\min )$ is the minimum input swing for which AC parameters are guaranteed. The device has a DC gain of $\approx 40$.


Figure 2. TTL Output Loading Used for Device Evaluation
Resource Reference of Application Notes
AN1405/D - ECL Clock Distribution Techniques
AN1406/D - Designing with PECL (ECL at +5.0 V)
AN1503/D - ECLinPS $^{m}$ I/O SPiCE Modeling Kit
AN1504/D - Metastability and the ECLinPS Family
AN1568/D - Interfacing Between LVDS and ECL
AN1672/D - The ECL Translator Guide
AND8001/D - Odd Number Counters Design
AND8002/D - Marking and Date Codes
AND8020/D - Termination of ECL Logic Devices
AND8066/D - Interfacing with ECLinPS
AND8090/D - AC Characteristics of ECL Devices


SOIC-8 NB
CASE 751-07
ISSUE AK
SCALE 1:1
DATE 16 FEB 2011


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW
7. 751-01 THRU 751-06 AR
STANDARD IS 751-07.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC |  | 0.050 BSC |  |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |
|  | $\circ$ | 8 |  |  |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

## GENERIC

MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
= Year
$\begin{array}{ll}\mathrm{W} & =\text { Work Week } \\ \text { - } & =\text { Pb-Free Package }\end{array}$
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{=}$ ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## STYLES ON PAGE 2

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SOIC-8 NB
CASE 751-07
ISSUE AK
DATE 16 FEB 2011

STYLE

| PIN 1. | EMITTER |
| ---: | :--- |
| 2. | COLLECTOR |
| 3. | COLLECTOR |
| 4. | EMITTER |
| 5. | EMITTER |
| 6. | BASE |
| 7. | BASE |
| 8. | EMITTER |
| STYLE 5: |  |
| PIN 1. | DRAIN |
| 2. | DRAIN |
| 3. | DRAIN |
| 4. | DRAIN |
| 5. | GATE |
| 6. | GATE |
| 7. | SOURCE |
| 8. | SOURCE |

STYLE 9:
PIN 1. EMITTER, COMMON
COLLECTOR, DIE \#1 COLLECTOR, DIE \#2 EMITTER, COMMON EMITTER, COMMON BASE, DIE \#2
BASE, DIE \#1
8. EMITTER, COMMON

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE

GATE
DRAIN
DRAIN
DRAIN
8. DRAIN

STYLE 17:
PIN 1. VCC
V2OUT
V10UT
V10UT
TXE
RXE
VEE
7. GND
8. ACC

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3

CATHODE 4
CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 25:
PIN 1. VIN
2. $\mathrm{N} / \mathrm{C}$

REXT
GND
IOUT
IOUT
IOUT
8. IOUT

## STYLE 29

PIN 1. BASE, DIE \#
EMITTER, \#1
BASE, \#2
. EMITTER, \#2
5. COLLECTOR, \#2
6. COLLECTOR, \#2
7. COLLECTOR, \#1
8. COLLECTOR, \#1

STYLE
PIN 1. COLIECTOR,
2. COLLECTOR, \#
3. COLLECTOR, \#2

COLLECTOR, \#2
BASE, \#2
. EMITTER, \#2
7. BASE, \#1
8. EMITTER, \#1

STYLE 6:
PIN 1. SOURCE
DRAIN
3. DRAIN
4. SOURCE

SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT

GROUND
GROUND
BIAS 2
7. INPUT
8. GROUND

STYLE 14
PIN 1. N-SOURCE
2. N-GATE
. P-SOURCE
P-GATE
5.DRAIN
6. P-DRAIN
7. N-DRAIN
8. N -DRAIN

STYLE 18
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 22 :
PIN 1. I/O LINE
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 26:
PIN 1. GND
2. $\mathrm{dv} / \mathrm{dt}$
3. ENABLE
4. ILIMIT

SOURCE
SOURCE
SOURCE
8. VCC

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
. SOURCE 1/DRAIN 2
SOURCE 1/DRAIN 2
8. GATE 1

STYLE 3
STYLE
2. DRAIN, DIE
2. DRAIN, \#1
2. DRAIN, \#
3. DRAIN, \#2
4. DRAIN, \#2
5. GATE, \#2
7. GATE, \#1
8. SOURCE, \#1

## STYLE 7

PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

## STYLE 11:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

## STYLE 15:

PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

## STYLE 19:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

## STYLE 23:

PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
8. COMMON CATHODE

## STYLE 8:

PIN 1. COLLECTOR, DIE \#1
2. BASE, \#1
3. BASE, \#2
4. COLLECTOR, \#2
5. COLLECTOR, \#2
6. EMITTER, \#2
7. EMITTER, \#1
8. COLLECTOR, \#1

## STYLE 12

PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 16:

PIN 1. EMITTER, DIE \#1
2. BASE, DIE \#1
3. EMITTER, DIE \#2
3. EMITTER, DIE
4. BASE, DIE \#2
4. BASE, DIE \#2
6. COLLECTOR, DIE \#2
7. COLLECTOR, DIE \#1
8. COLLECTOR, DIE \#1

## STYLE 20:

PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 24
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

## STYLE 28:

PIN 1. SW_TO_GND
2. DASIC $\bar{O} F F$
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

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TSSOP 8

## CASE 948R-02

ISSUE A
DATE 04/07/2000

## SCALE 2:1


notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PROTRUSI
PER SIDE
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

|  | MILLIMETERS |  | INCHES |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | MAX | MIN | MAX |  |  |
| A | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| B | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| C | 0.80 | 1.10 | 0.031 | 0.043 |  |  |
| D | 0.05 | 0.15 | 0.002 | 0.006 |  |  |
| F | 0.40 | 0.70 | 0.016 | 0.028 |  |  |
| G | 0.65 BSC |  | 0.026 BSC |  |  |  |
| K | 0.25 |  | 0.40 | 0.010 |  | 0.016 |
| L | 4.90 BSC |  | 0.193 BSC |  |  |  |
| M | $0^{\circ}$ |  | $6^{\circ}$ | $0^{\circ}$ |  | $6^{\circ}$ |


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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | TSSOP 8 | PAGE 1 OF 1 |

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